

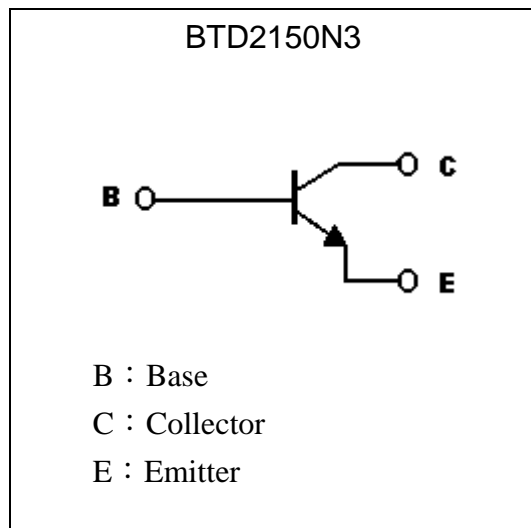
Low $V_{CE(sat)}$ NPN Epitaxial Planar Transistor
BTD2150N3

BV_{CEO}	50V
I_C	4A
$R_{CE(SAT)}$ typ.	90m Ω

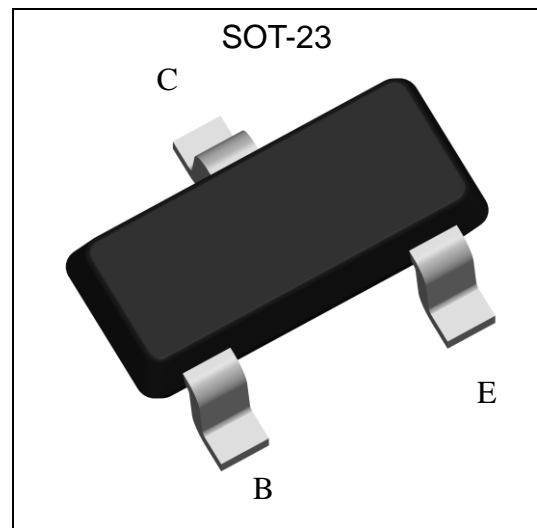
Features

- Low $V_{CE(sat)}$, typically 0.18V at $I_C / I_B = 2A / 0.1A$
- Excellent current gain characteristics
- Complementary to BTB1424N3
- Pb-free lead plating and halogen-free package

Symbol

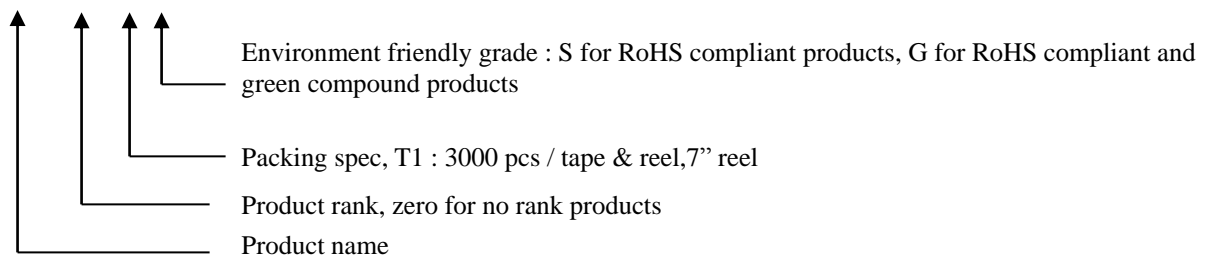


Outline



Ordering Information

Device	Package	Shipping
BTD2150N3-X-T1-G	SOT-23 (Pb-free lead plating and halogen-free package)	3000 pcs / tape & reel





Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Limit	Unit
Collector-Base Voltage	V _{CBO}	80	V
Collector-Emitter Voltage	V _{CEO}	50	
Emitter-Base Voltage	V _{EBO}	6	
Collector Current (DC)	I _C	4	A
Collector Current (Pulse)	I _{CP}	7 (Note 1)	
Power Dissipation	P _D	225	mW
		660 (Note 2)	
Thermal Resistance, Junction to Ambient	R _{θJA}	556	°C/W
		190	
Operating Junction and Storage Temperature Range	T _j ; T _{stg}	-55~+150	°C

Note : 1. Single Pulse P_w ≤ 350μs, Duty ≤ 2%.

2. Device mounted on an FR-4 PCB, single sided copper, tin plated, mounting pad for collector 1cm².

Characteristics (Ta=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV _{CBO}	80	-	-	V	I _C =100μA, I _E =0
BV _{CEO}	50	-	-	V	I _C =1mA, I _B =0
BV _{EBO}	6	-	-	V	I _E =50μA, I _C =0
I _{CBO}	-	-	100	nA	V _{CB} =80V, I _E =0
I _{EBO}	-	-	100	nA	V _{EB} =6V, I _C =0
*V _{CE(sat)}	-	40	100	mV	I _C =400mA, I _B =20mA
*V _{CE(sat)}	-	160	220	mV	I _C =1A, I _B =10mA
*V _{CE(sat)}	-	180	320	mV	I _C =2A, I _B =100mA
*R _{CE(sat)}	-	90	160	mΩ	I _C =2A, I _B =100mA
*V _{BE(sat)}	-	0.94	1.3	V	I _C =2A, I _B =200mA
*h _{FE1}	200	-	-	-	V _{CE} =2V, I _C =100mA
*h _{FE2}	270	-	820	-	V _{CE} =2V, I _C =500mA
*h _{FE3}	100	-	-	-	V _{CE} =2V, I _C =1A
f _T	-	175	-	MHz	V _{CE} =1V, I _C =0.1A, f=100MHz
Cob	-	14	-	pF	V _{CB} =10V, f=1MHz

*Pulse Test : Pulse Width ≤ 380μs, Duty Cycle ≤ 2%

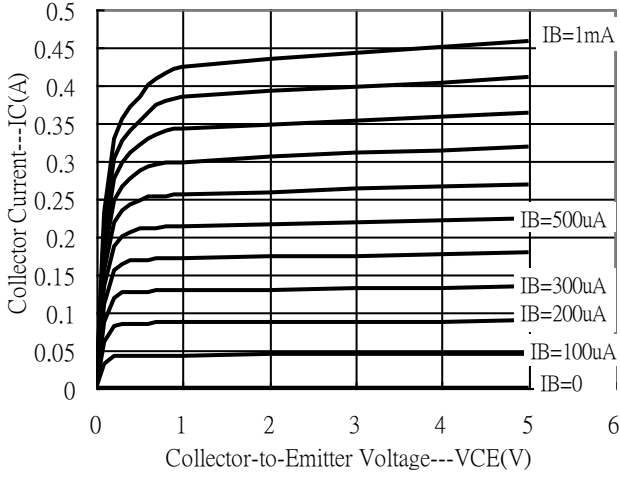
Classification Of hFE 2

Rank	S	T
Range	270~560	390~820

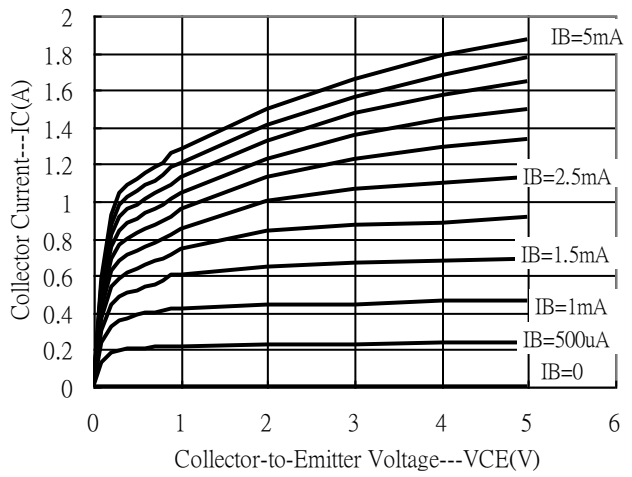


Typical Characteristics

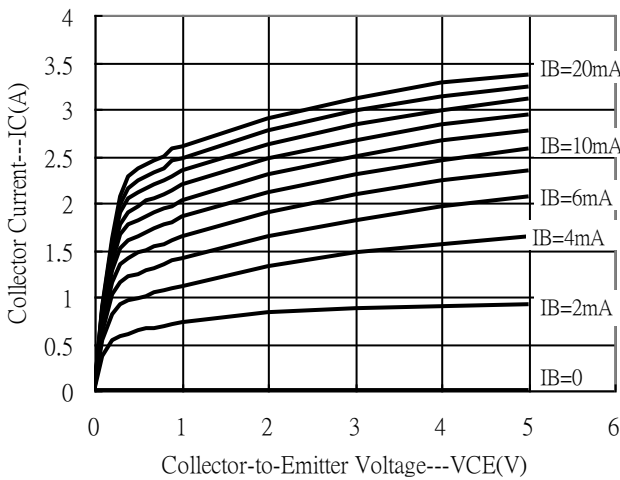
Emitter Grounded Output Characteristics



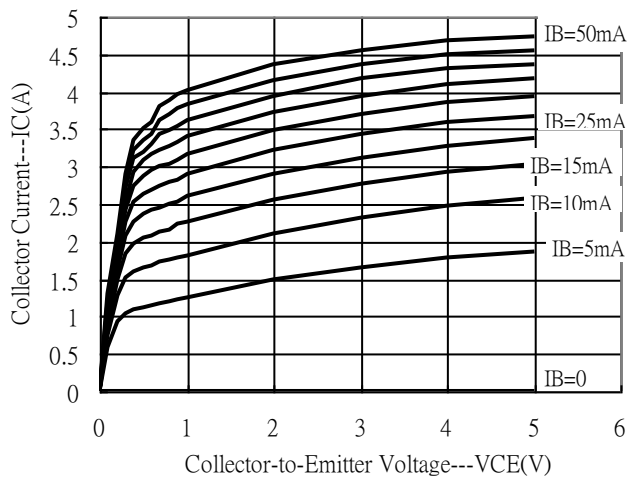
Emitter Grounded Output Characteristics



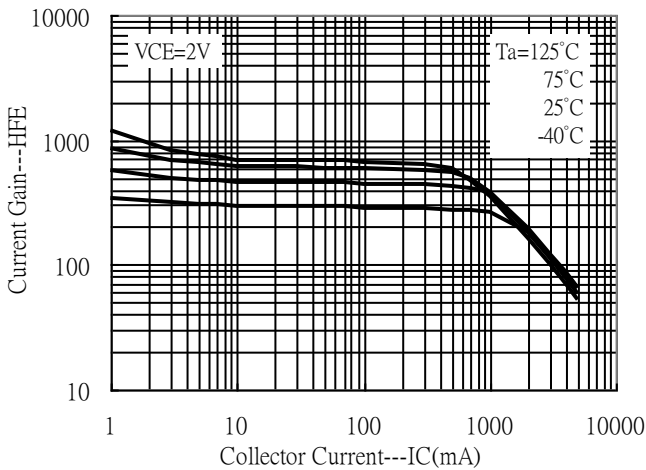
Emitter Grounded Output Characteristics



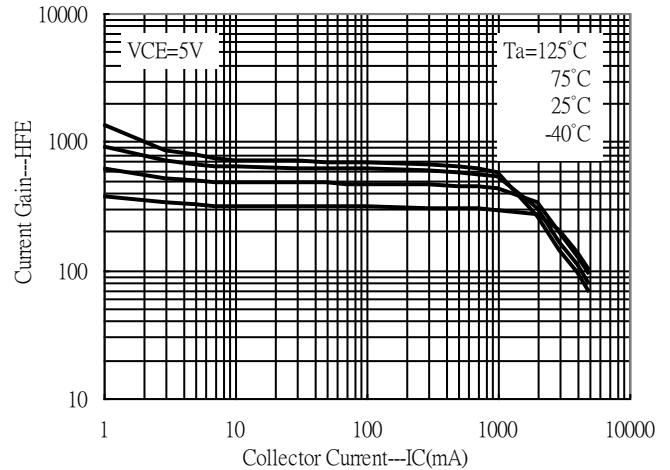
Emitter Grounded Output Characteristics



Current Gain vs Collector Current



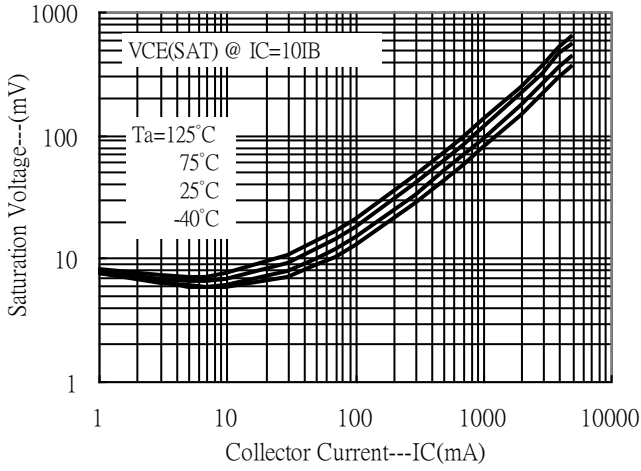
Current Gain vs Collector Current



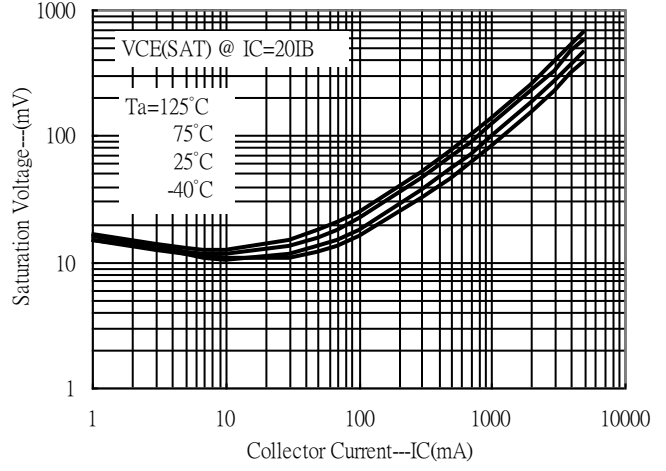


Typical Characteristics(Cont.)

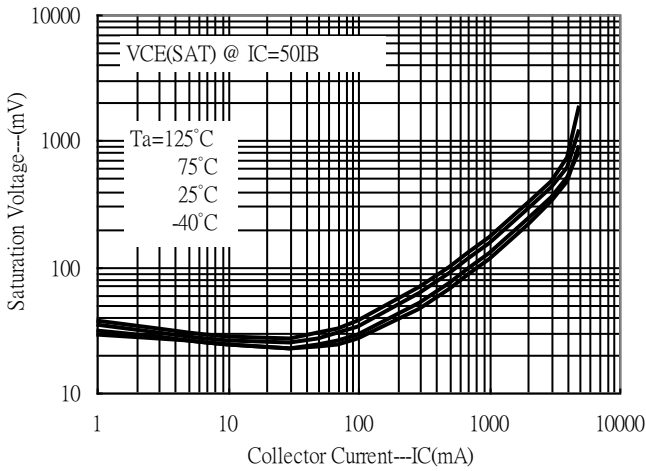
Saturation Voltage vs Collector Current



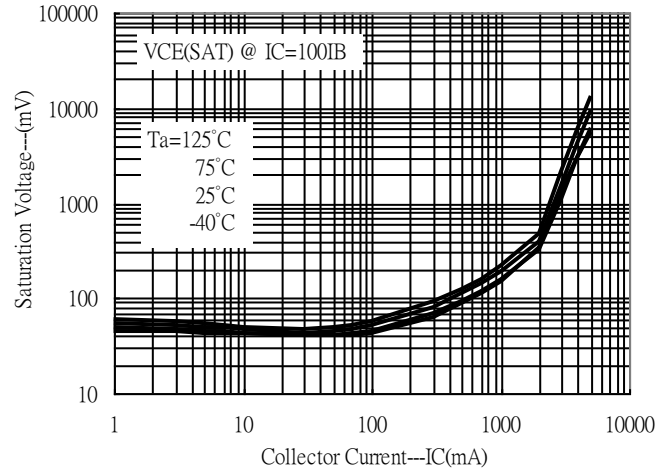
Saturation Voltage vs Collector Current



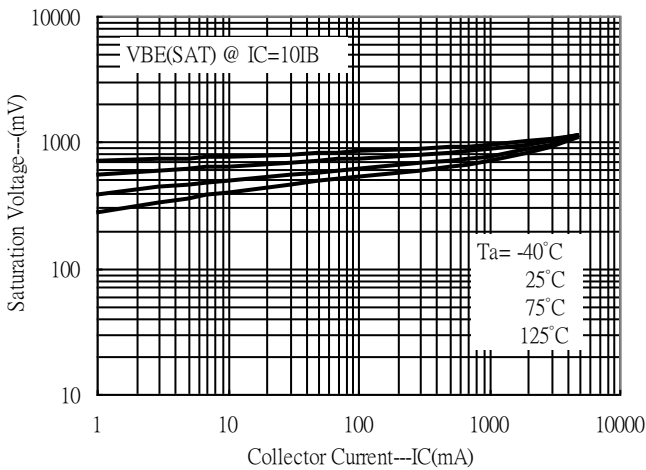
Saturation Voltage vs Collector Current



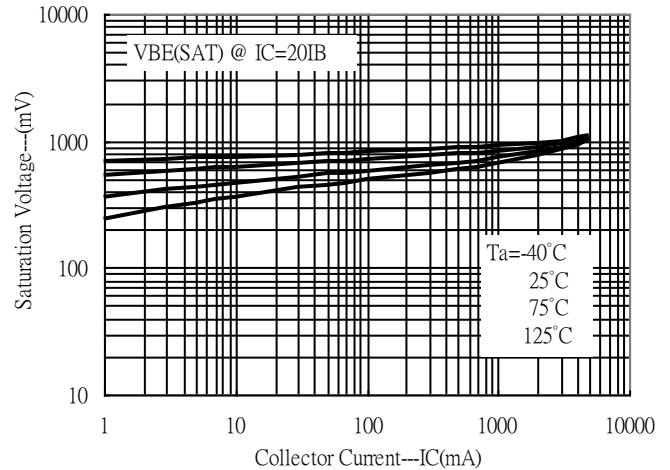
Saturation Voltage vs Collector Current



Saturation Voltage vs Collector Current



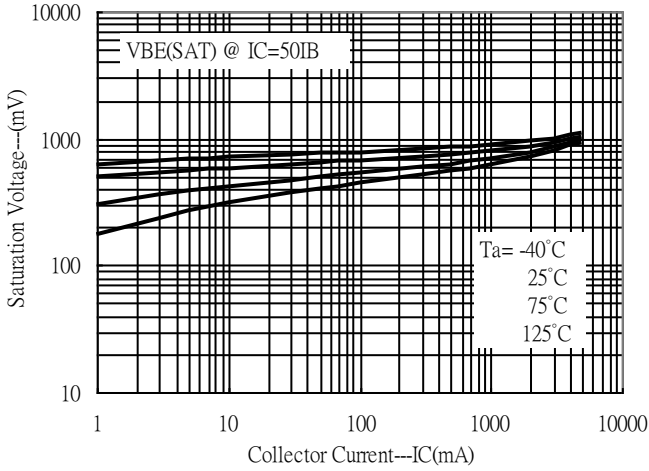
Saturation Voltage vs Collector Current



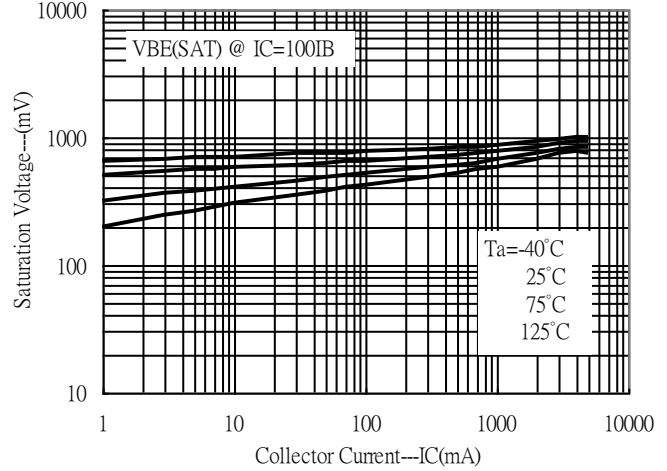


Typical Characteristics(Cont.)

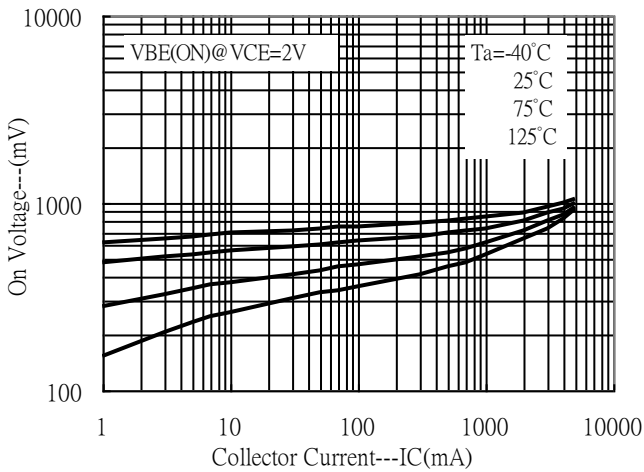
Saturation Voltage vs Collector Current



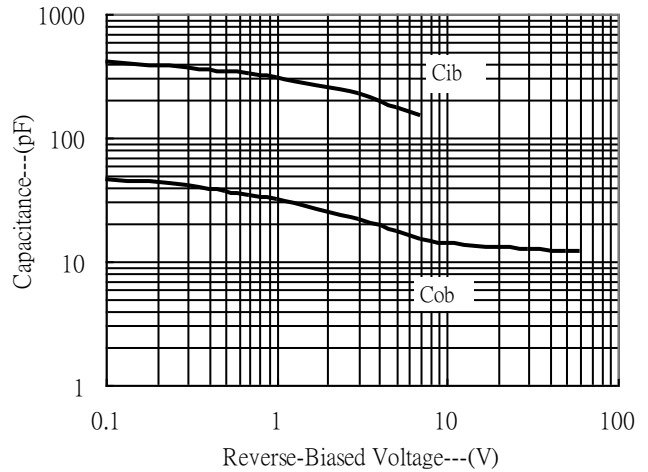
Saturation Voltage vs Collector Current



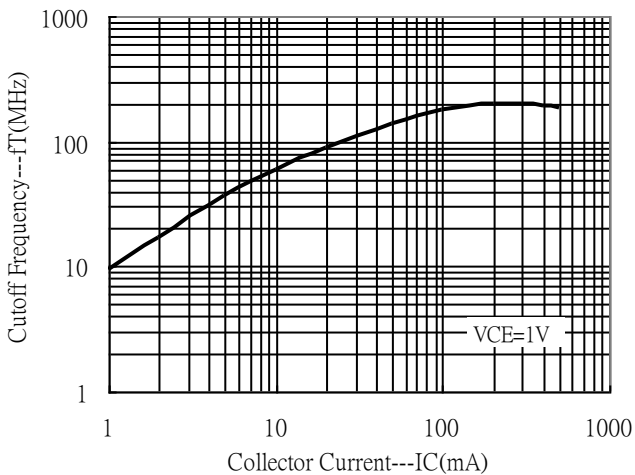
On Voltage vs Collector Current



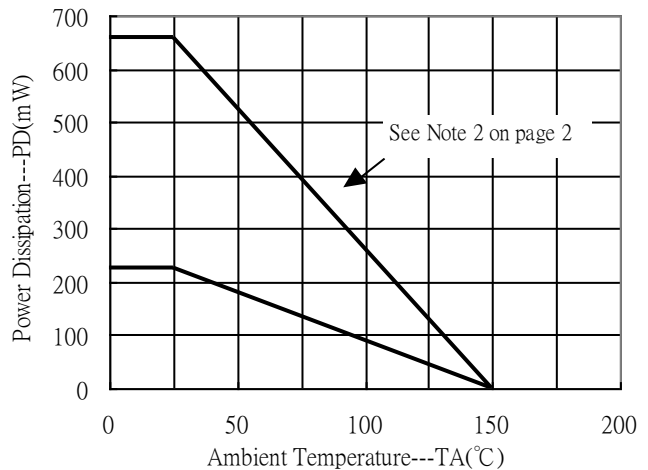
Capacitance vs Reverse-Biased Voltage



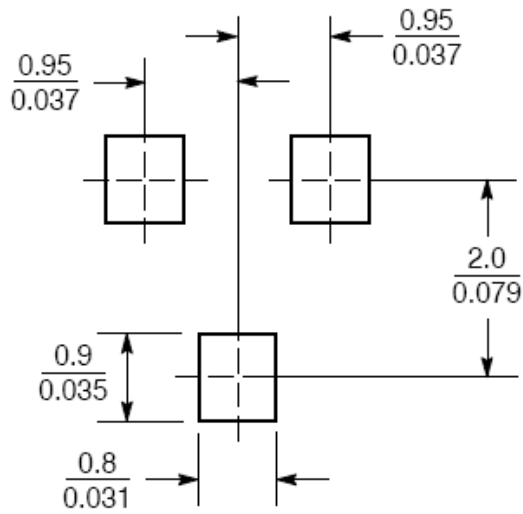
Cutoff frequency vs Collector Current



Power Derating Curve

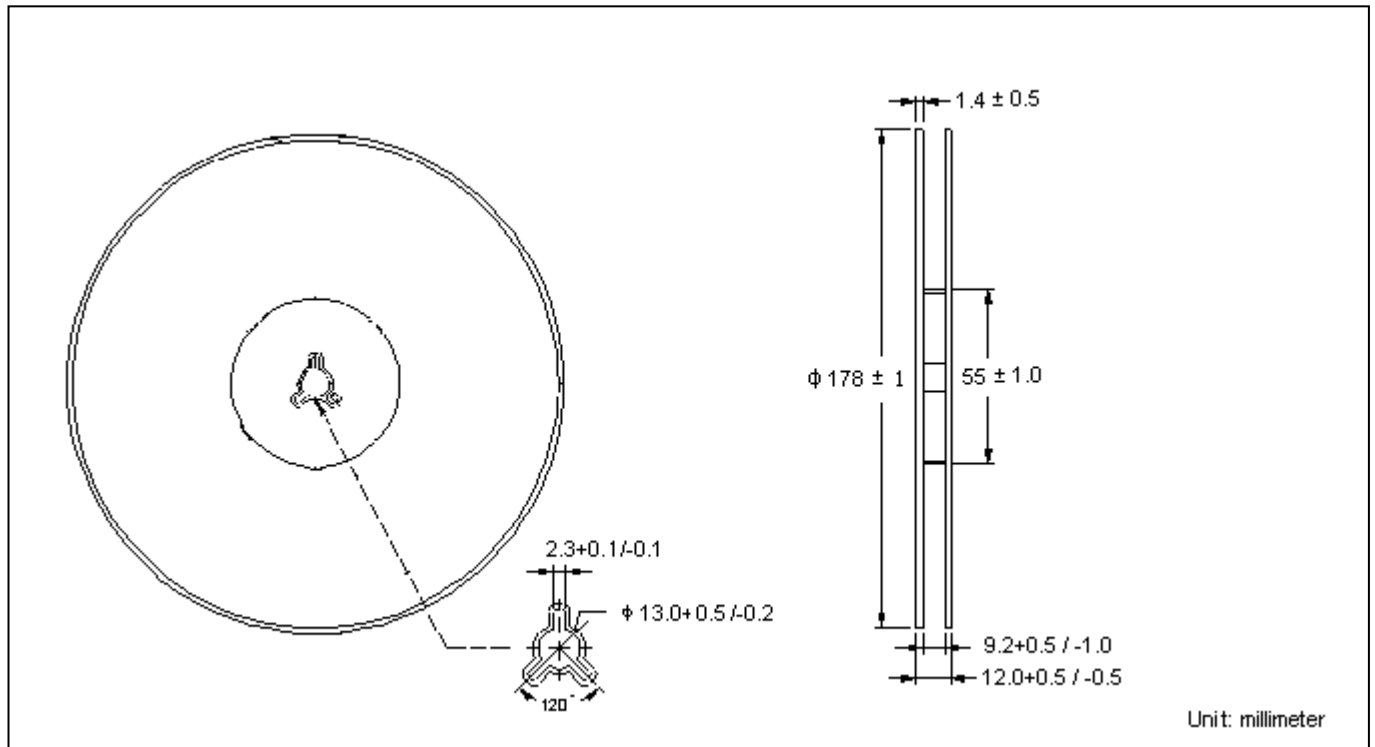


Recommended Soldering Footprint

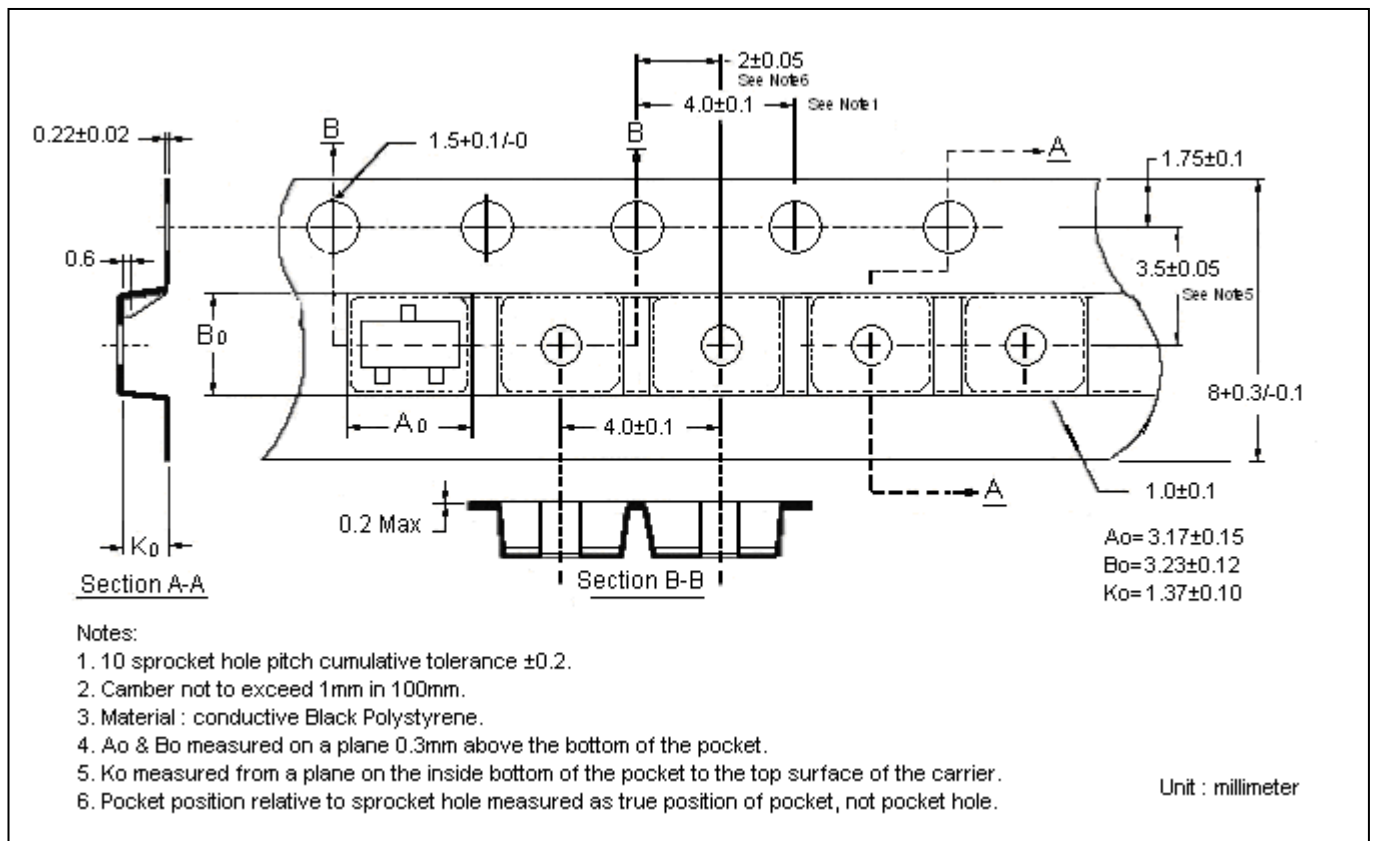


Unit : $\frac{\text{mm}}{\text{inches}}$

Reel Dimension



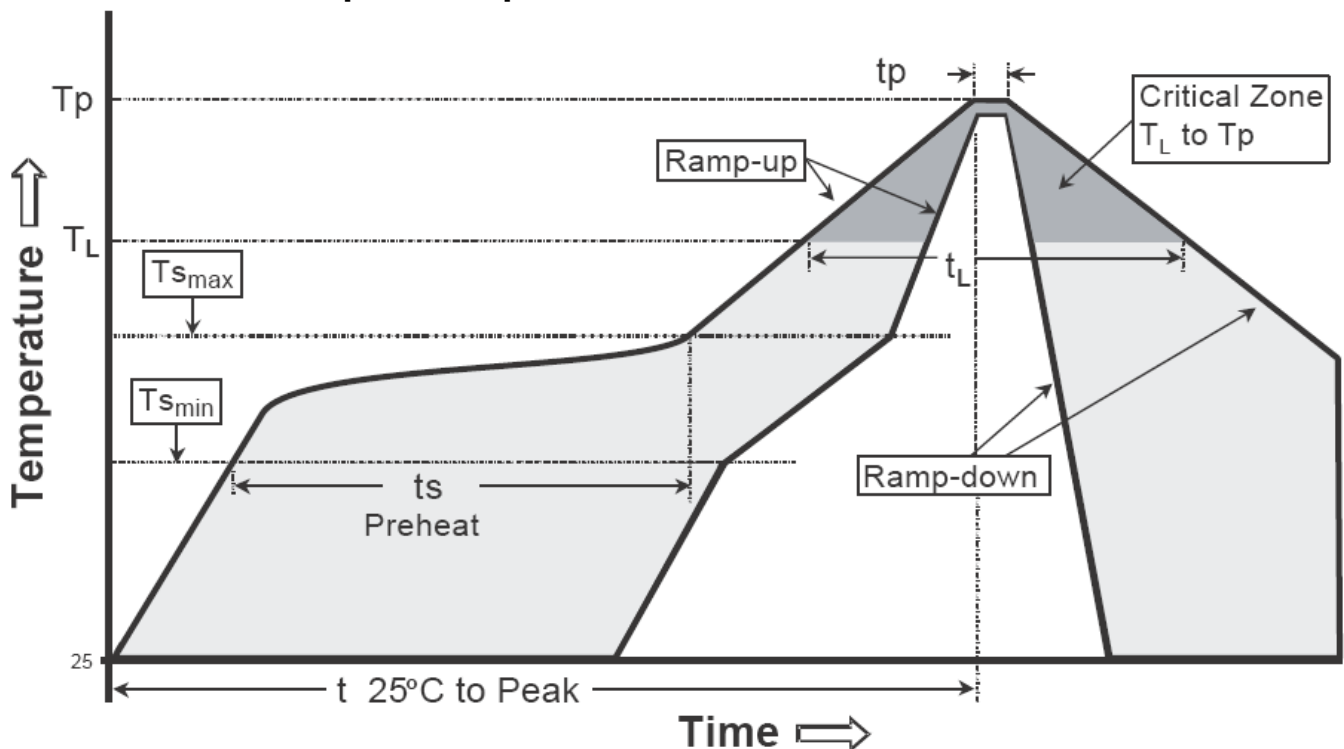
Carrier Tape Dimension



Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

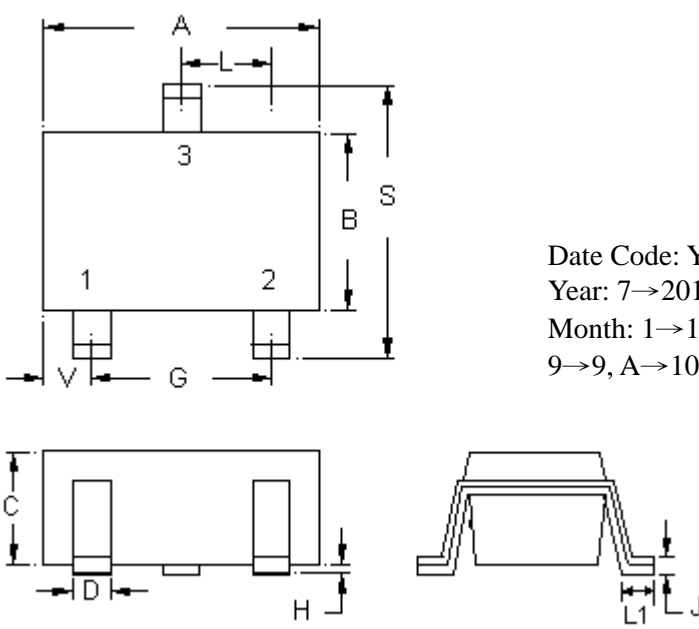
Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (T _{smax} to T _p)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(T _{s min})	100°C	150°C
-Temperature Max(T _{s max})	150°C	200°C
-Time(t _{s min} to t _{s max})	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (T _L)	183°C	217°C
- Time (t _L)	60-150 seconds	60-150 seconds
Peak Temperature(T _p)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

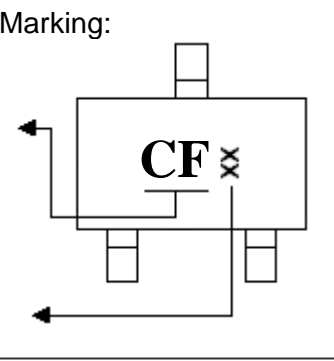
SOT-23 Dimension



Product Code

Date Code: Year+Month
 Year: 7→2017, 8→2018
 Month: 1→1, 2→2, . . .
 9→9, A→10, B→11, C→12

Marking:



3-Lead SOT-23 Plastic
 Surface Mounted Package
 CYStek Package Code: N3

Style : Pin 1.Base 2.Emitter 3.Collector

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1110	0.1189	2.82	3.02	J	0.0039	0.0079	0.10	0.20
B	0.0590	0.0669	1.50	1.70	L	0.0374	TYP	0.95	TYP
C	0.0413	0.0453	1.05	1.15	L1	0.0118	0.0236	0.30	0.60
D	0.0118	0.0197	0.30	0.50	S	0.1043	0.1161	2.65	2.95
G	0.0709	0.0787	1.80	2.00	V	0.0098	0.0256	0.25	0.65
H	0.0000	0.0040	0.00	0.10					

Notes: 1.Controlling dimension: millimeters.
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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